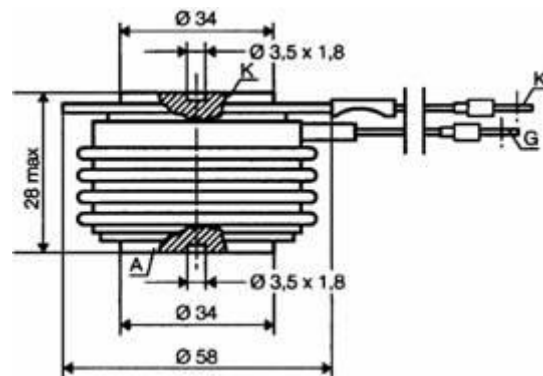




I <sub>L</sub>	Latching current	A	8	T <sub>vj</sub> =25°C; U <sub>D</sub> =12V, Gate pulse: 10V, 5Ω, 1μs rise time, 10μs
I <sub>H</sub>	Holding current	A	1,0	T <sub>vj</sub> =25°C; U <sub>D</sub> =12, Gate open
U <sub>GT</sub>	Gate trigger direct voltage	V	2,5	T <sub>vj</sub> =25°C; U <sub>D</sub> =12V
I <sub>GT</sub>	Gate trigger direct current	A	0,3	T <sub>vj</sub> =25°C; U <sub>D</sub> =12V
U <sub>GD</sub>	Gate non-trigger direct voltage	V	0,25	T <sub>vj</sub> =125°C; U <sub>D</sub> =0,67 U <sub>DRM</sub>
t <sub>gd</sub>	Delay time	μs	2,0	T <sub>vj</sub> =25°C, U <sub>D</sub> =500V, I <sub>TM</sub> =500A Gate pulse: 10V, 5Ω, 1μs rise time, 10μs
t <sub>gt</sub>	Turn-on time	μs	3,2	
t <sub>q</sub>	Turn-off time	μs	16÷25 20÷32	T <sub>vj</sub> =125°C, I <sub>TM</sub> =500A, di <sub>R</sub> /dt= 10 A/μs U <sub>R</sub> =100V U <sub>D</sub> =0,67 U <sub>DRM</sub> Di <sub>D</sub> /dt= 50 A/μs Di <sub>D</sub> /dt= 200 A/μs
Q <sub>rr</sub>	Recovered charge	μC	100	T <sub>vj</sub> =125°C, I <sub>TM</sub> =500A, di <sub>R</sub> /dt= 50 A/μs, U <sub>R</sub> =100V
(di <sub>D</sub> /dt) cr	Critical rate of rise of off-state voltage	V/μs	500 1000	T <sub>vj</sub> =125°C; U <sub>D</sub> =0,67 U <sub>DRM</sub> Gate open
R <sub>thjc</sub>	Thermal resistance junction to case	°C/W	0,032	Direct current, double side cooled

Mounting force : 13 ÷ 19 kN  
Weight : 340 gram



SHANDOR Ltd. - POWER SEMICONDUCTORS DEVICES - shandor (at) bgb.bg - + 359 898 528828